TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

GT30J324

High Power Switching Applications

Fast Switching Applications

- Fourth-generation IGBT
- Enhancement mode type
- Fast switching (FS): Operating frequency up to 50 kHz (reference) High speed: $t_f = 0.05 \mu s$ (typ.)

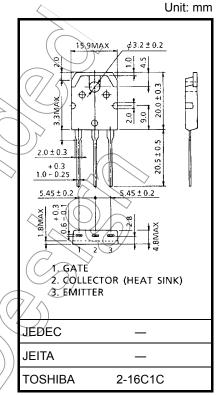
Low switching loss: $E_{on} = 1.00 \text{ mJ (typ.)}$

 $: E_{off} = 0.80 \text{ mJ (typ.)}$

- Low saturation voltage: VCE (sat) = 2.0 V (typ.)
- FRD included between emitter and collector

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	600	> V	
Gate-emitter voltage		V_{GES}	±20	V	
Collector current	DC	IC	30	А	
	1 ms	ICP	60		
Emitter-collector forward current	DC	lF	30	A	
	1 ms	I _{FM}	60		
Collector power dissipation (Tc = 25°C)		PC	170	w	
Junction temperature		((T _j \)	150	∕/°c	
Storage temperature range		Tstg	-55 to 150	7.6	



Weight: 4.6 g (typ.)

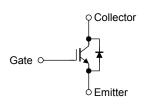
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

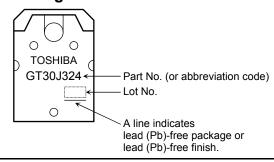
Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance (IGBT)	R _{th} (j-c)	0.735	°C/W
Thermal resistance (diode)	R _{th (j-c)}	1.90	°C/W

Equivalent Circuit



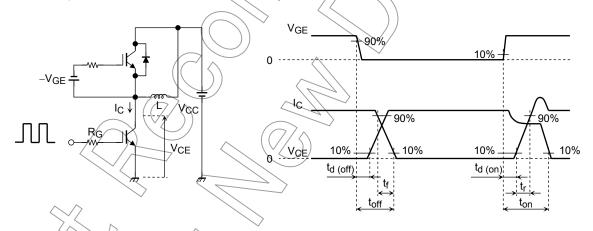
Marking



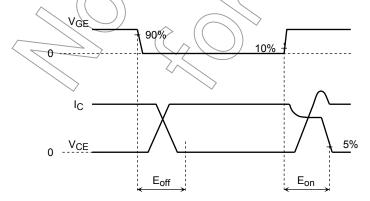
Electrical Characteristics (Ta = 25°C)

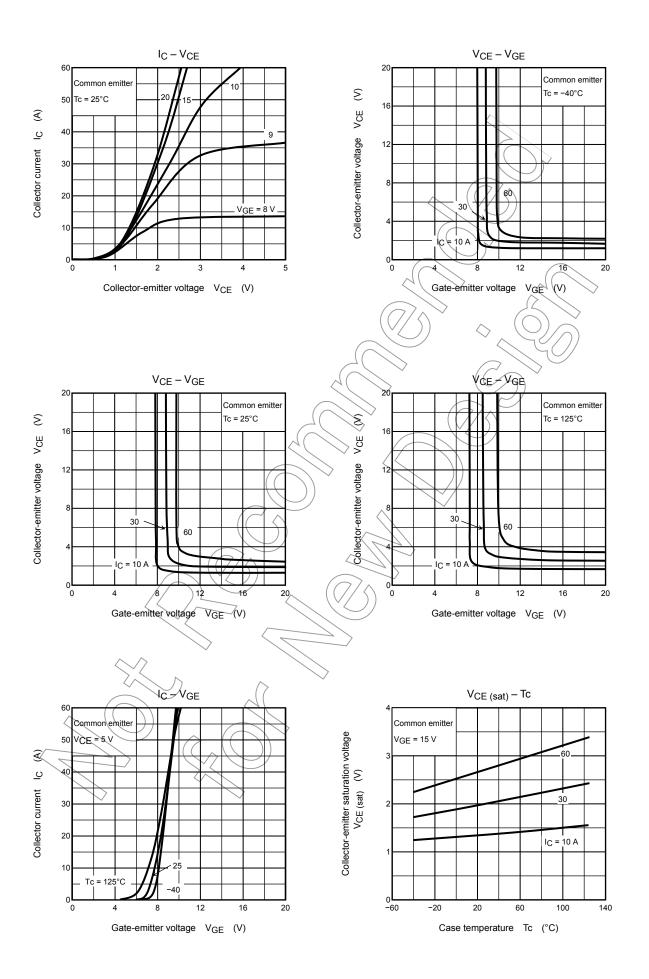
Cha	racteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I _{GES}	V _{GE} = ±20 V, V _{CE} = 0	_	_	±500	nA
Collector cut-off	current	I _{CES}	V _{CE} = 600 V, V _{GE} = 0	_	_	1.0	mA
Gate-emitter cur	t-off voltage	V _{GE} (OFF)	I _C = 3 mA, V _{CE} = 5 V	3.5	_	6.5	V
Collector-emitte	r saturation voltage	V _{CE} (sat)	I _C = 30 A, V _{GE} = 15 V		2.0	2.45	V
Input capacitano	ce	C _{ies}	V _{CE} = 10 V, V _{GE} = 0, f = 1 MHz	F	4650	_	pF
Switching time	Turn-on delay time	t _{d (on)}	Inductive Load V_{CC} = 300 V, I_{C} = 30 A V_{GG} = +15 V, R_{G} = 24 Ω (Note 1) (Note 2)) 	0.09	_	μs
	Rise time	t _r		<i>))</i>	0.07	_	
	Turn-on time	t _{on}		, –	0.24	_	
	Turn-off delay time	t _{d (off)}		_	0.30	_	
	Fall time	t _f		-	0.05	\nearrow	
	Turn-off time	t _{off}		- (0.43	> -	
Switching loss	Turn-on switching loss	E _{on}	(Note 2)		1.00) –	mJ
	Turn-off switching loss	E _{off}		7	0.80		1113
Peak forward vo	oltage	V _F	I _F = 30 A, V _{GE} = 0		_	3.8	V
Reverse recove	ry time	t _{rr}	I _F = 30 A, di/dt = -100 A/μs	<u> </u>	60	_	ns

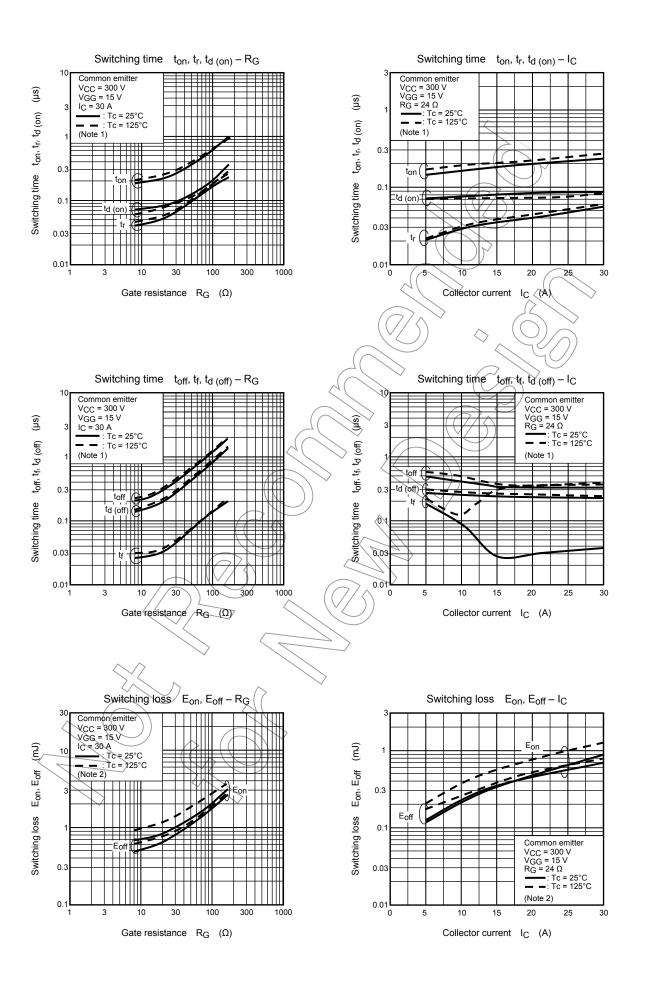
Note 1: Switching time measurement circuit and input/output waveforms

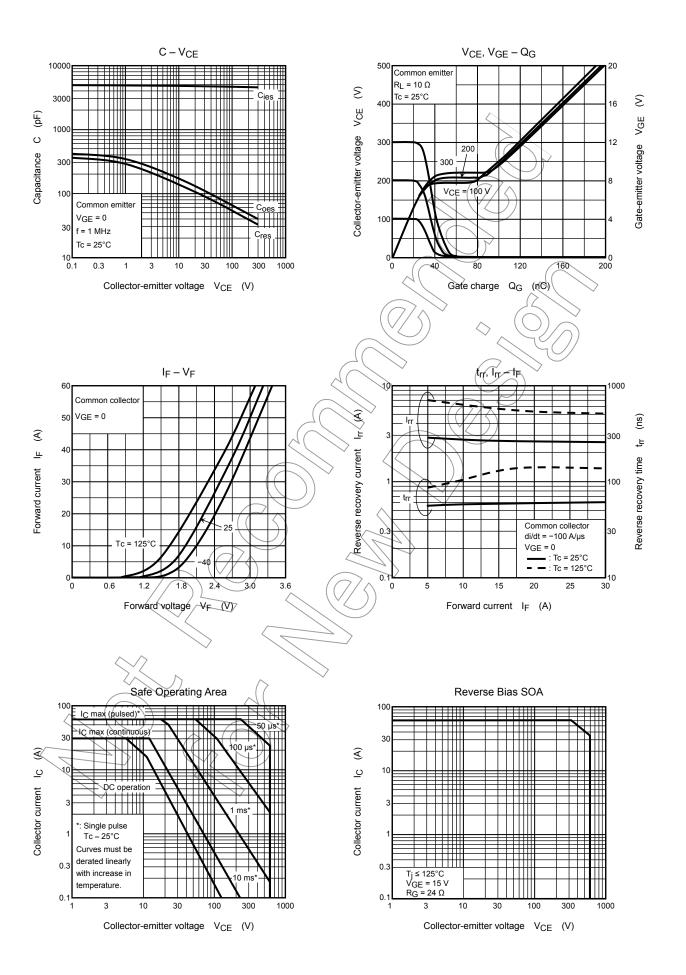


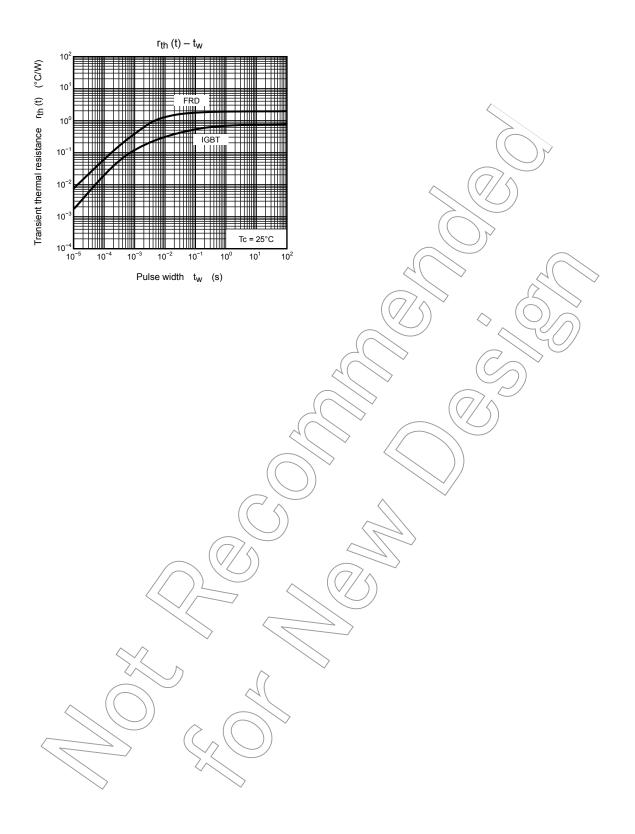
Note 2: Switching loss measurement waveforms











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